PATENT ASSIGNMENT

Electronic Version v1.1 Stylesheet Version v1.1

SUBMISSION TYPE: NEW ASSIGNMENT

NATURE OF CONVEYANCE: SECURITY AGREEMENT

CONVEYING PARTY DATA

Name	Execution Date
DIODES FABTECH INC., as Grantor	01/08/2013

RECEIVING PARTY DATA

Name:	BANK OF AMERICA, N.A., AS ADMINISTRATIVE AGENT	
Street Address:	901 Main Street, 14th Fl.	
Internal Address:	(Mail Code: TX1-492-14-12)	
City:	Dallas	
State/Country:	TEXAS	
Postal Code:	75202-3714	

PROPERTY NUMBERS Total: 8

Property Type	Number
Patent Number:	7709864
Patent Number:	7847315
Patent Number:	6376346
Patent Number:	6362112
Patent Number:	6717229
Patent Number:	6462393
Patent Number:	6797992
Application Number:	12869940

CORRESPONDENCE DATA

Fax Number: 2122944700

Correspondence will be sent via US Mail when the fax attempt is unsuccessful.

Phone: 2122946635

Email: dkumar@winston.com

Correspondent Name: WINSTON & STRAWN LLP - Patrick Strubbe

Address Line 1: 1700 K Street N.W.

PATENT

REEL: 029594 FRAME: 0139

502188358

Address Line 2: Patent Department
Address Line 4: Washington, DISTRICT OF COLUMBIA 200063817

ATTORNEY DOCKET NUMBER: 3165.7096-DIODES FABTECH

NAME OF SUBMITTER: Peter Strubbe

Total Attachments: 5

source=BOA-3165-7096-Executed Notice of Grant of Secutiry Interest in Patents-Diodes Fabtech Inc#page1.tif source=BOA-3165-7096-Executed Notice of Grant of Secutiry Interest in Patents-Diodes Fabtech Inc#page2.tif source=BOA-3165-7096-Executed Notice of Grant of Secutiry Interest in Patents-Diodes Fabtech Inc#page3.tif source=BOA-3165-7096-Executed Notice of Grant of Secutiry Interest in Patents-Diodes Fabtech Inc#page4.tif source=BOA-3165-7096-Executed Notice of Grant of Secutiry Interest in Patents-Diodes Fabtech Inc#page5.tif

NOTICE OF GRANT OF SECURITY INTEREST IN PATENTS

January 8, 2013

United States Patent and Trademark Office

Ladies and Gentlemen:

Please be advised that pursuant to the Collateral Agreement dated as of January 8, 2013 (as amended, restated, supplemented or otherwise modified from time to time, the "Agreement") among the undersigned Grantor, the other grantors party thereto and the undersigned Administrative Agent (including any successors and assigns) for the Secured Parties referenced in the Agreement, the undersigned Grantor has granted a continuing security interest in and continuing lien upon the Patents, including the United States Patents identified on Schedule 1 hereto (the "Patent Collateral") to the Administrative Agent for the ratable benefit of the Secured Parties. Terms used herein but not otherwise defined herein shall have the meaning ascribed to them in the Agreement.

The Grantors and the Administrative Agent, on behalf of the Secured Parties, hereby acknowledge and agree that the grant of a security interest in the Patent Collateral (a) may only be terminated in accordance with the terms of the Agreement and (b) is not to be construed as an assignment of any patent or patent application.

This Notice of Grant of Security Interest in Patents has been entered into in conjunction with the provisions of the Agreement. The Grantor does hereby acknowledge and confirm that the grant of the security interest hereunder to, and the rights and remedies of, the Administrative Agent with respect to the Patent Collateral are more fully set forth in the Agreement, the terms and provisions of which are incorporated herein by reference as if fully set forth herein.

[Signature page follows]

CHL:59612.2

ADDRESS OF GRANTOR:

Diodes FabTech, Inc. 4949 Hedgecoxe Road, Suite 200 Plano, TX 75024 Very truly yours,

DIODES FABTECH INC.,

as Grantor

Name: Richard Dallas White

Title: Director

Diodes Incorporated
Signature Page
Notice of Grant in Security Interest in Patents

ADDRESS OF ADMINISTRATIVE AGENT:

Bank of America, N.A., as Administrative Agent

901 Main Street, 14t Fl Mail Code: TX1-492-14-12 Dallas, TX 75202-3714 Acknowledged and accepted:

BANK OF AMERICA, N.A.,

as Administrative Agent

Name: Title: Anthony W. Kell

Assistant Vice President

Diodes Incorporated Signature Page Notice of Grant in Security Interest in Patents

SCHEDULE 1

<u>PATENTS</u>			
Patent No.	Description of Patent Item	Date of Patent	
7,709,864	High-Efficiency Schottky Rectifier and Method of Manufacturing Same	May 4, 2010	
7,847,315	High Efficiency Rectifier	December 7, 2010	
6,376,346	High Voltage Device and Method for Making the Same	April 23, 2002	
6,362,112	Single Step Etched Moat	March 26, 2002	
6,717,229	Distributed Reverse Surge Guard	April 6, 2004	
6,462,393	Schottky Device	October 8, 2002	
6,797,992	Apparatus and Method for Fabricating a High Reverse Voltage Semiconductor Device	September 28, 2004	

CHL:59612.2

PATENT APPLICATIONS				
Patent Applications No.	Description of Patent Applied for	Date of Patent Applications		
12/869,940	Top Tri-Metal System for Silicon Power Semiconductor Devices	August 27, 2010		

CHL:59612.2